

Abstract

The present invention relates to a polishing pad which is characterized in that it is of micro rubber A-type hardness at least 80°, has closed cells of average cell diameter no more than 1000 μm , is of density in the range 0.4 to 1.1 and contains polyurethane and polymer produced from a vinyl compound. When planarizing local unevenness on a semiconductor substrate with the polishing pad relating to the present invention, the polishing rate is high, the global step height is low, dishing does not readily occur at the metallic interconnects, clogging and permanent set of the surface layer region do not readily occur and the polishing rate is stable.

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